

isc N-Channel MOSFET Transistor

IPI60R125CP

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤0.125Ω
- · Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

- · Ultra low gate charge
- High peak current capability

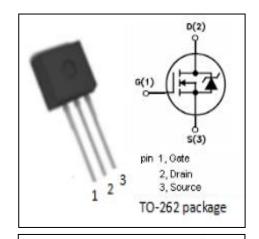


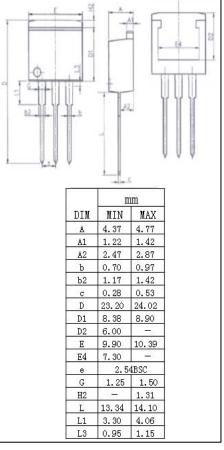
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

ADOCE TE INACINION TATITOO(Ta 20 0)						
SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	600	V			
V _{GS}	Gate-Source Voltage	±20	V			
I _D	Drain Current-Continuous 25		А			
I _{DM}	Drain Current-Single Pulsed 82		А			
P _D	Total Dissipation @T _C =25℃ 208		W			
Tj	Max. Operating Junction Temperature 150		$^{\circ}$			
T _{stg}	Storage Temperature	-55~150	$^{\circ}$			

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.6	°C/W







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =1.1mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; ID=16A			0.125	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			2	μА
V _{SD}	Diode forward voltage	I _F =16A; V _{GS} = 0V			1.2	V

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